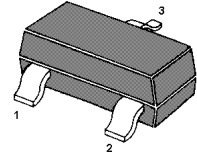


## BC807 TRANSISTOR(PNP)

### FEATURES

- Ideally Suited for Automatic Insertion
- Epitaxial Planar Die Construction
- For Switching, AF Driver and Amplifier Applications
- Complementary NPN Types Available (BC817)

#### SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

**MARKING:BC807-16:5A**  
**BC807-25:5B**  
**BC807-40:5C**

### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.5	A
P <sub>C</sub>	Collector Power Dissipation	0.3	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> =0	-50		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-45		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -1μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -45V, I <sub>E</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4 V, I <sub>C</sub> =0		-0.1	μA
DC current gain	807-16 807-25 807-40	h <sub>FE(1)</sub> V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	100 160 250	250 400 600	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> = -50mA		-0.7	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f=100MHz	100		MHz

TYPICAL CHARACTERISTICS

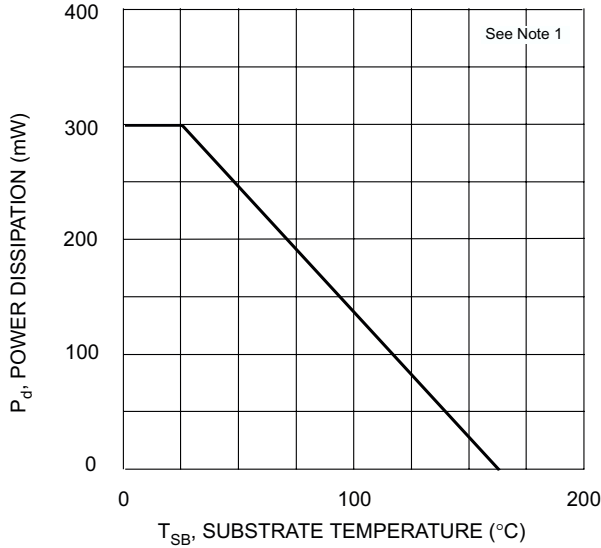


Fig. 1, Power Derating Curve

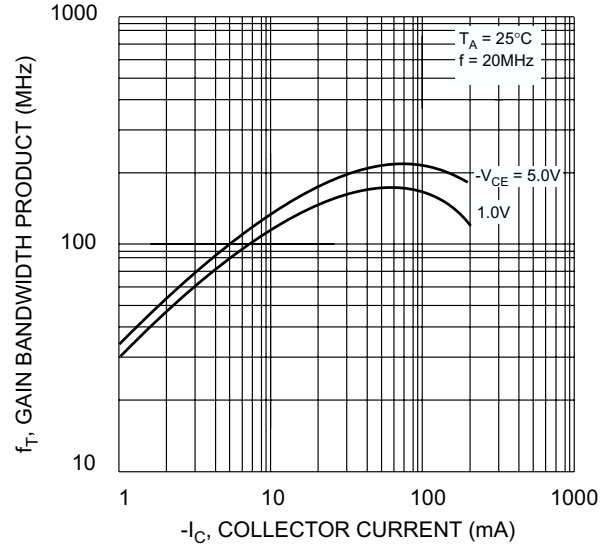


Fig. 2, Gain-Bandwidth Product vs Collector Current

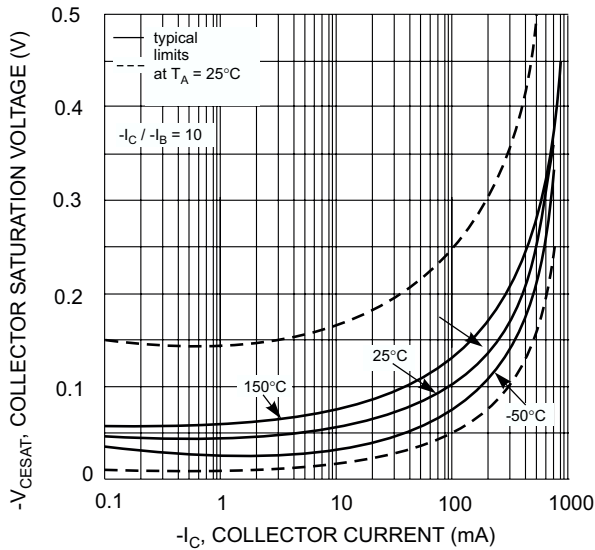


Fig. 3, Collector Sat. Voltage vs Collector Current

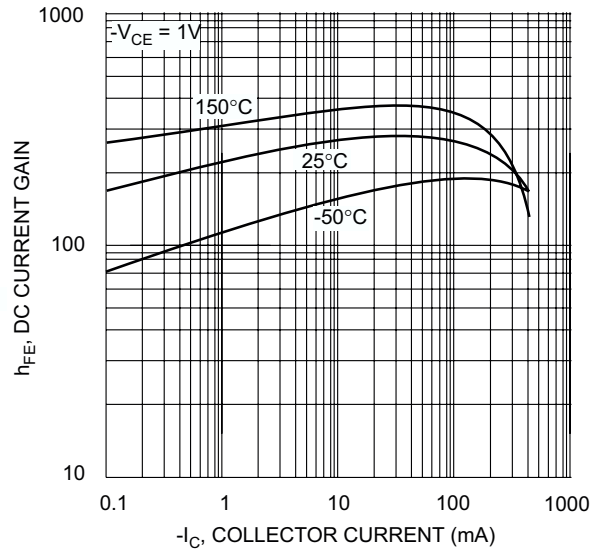


Fig. 4, DC Current Gain vs Collector Current

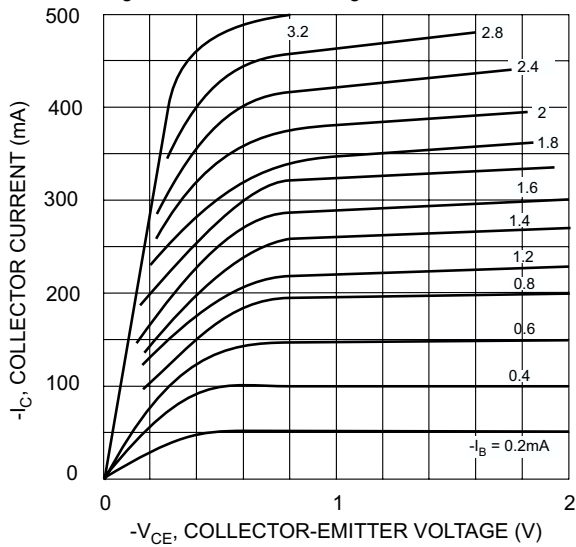


Fig. 5, Typical Emitter-Collector Characteristics

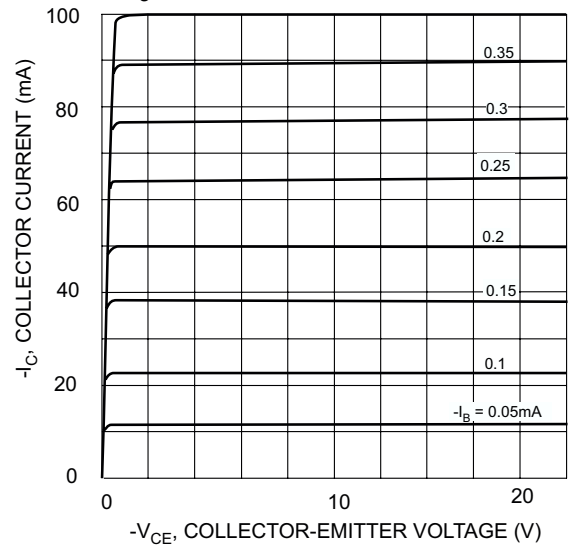
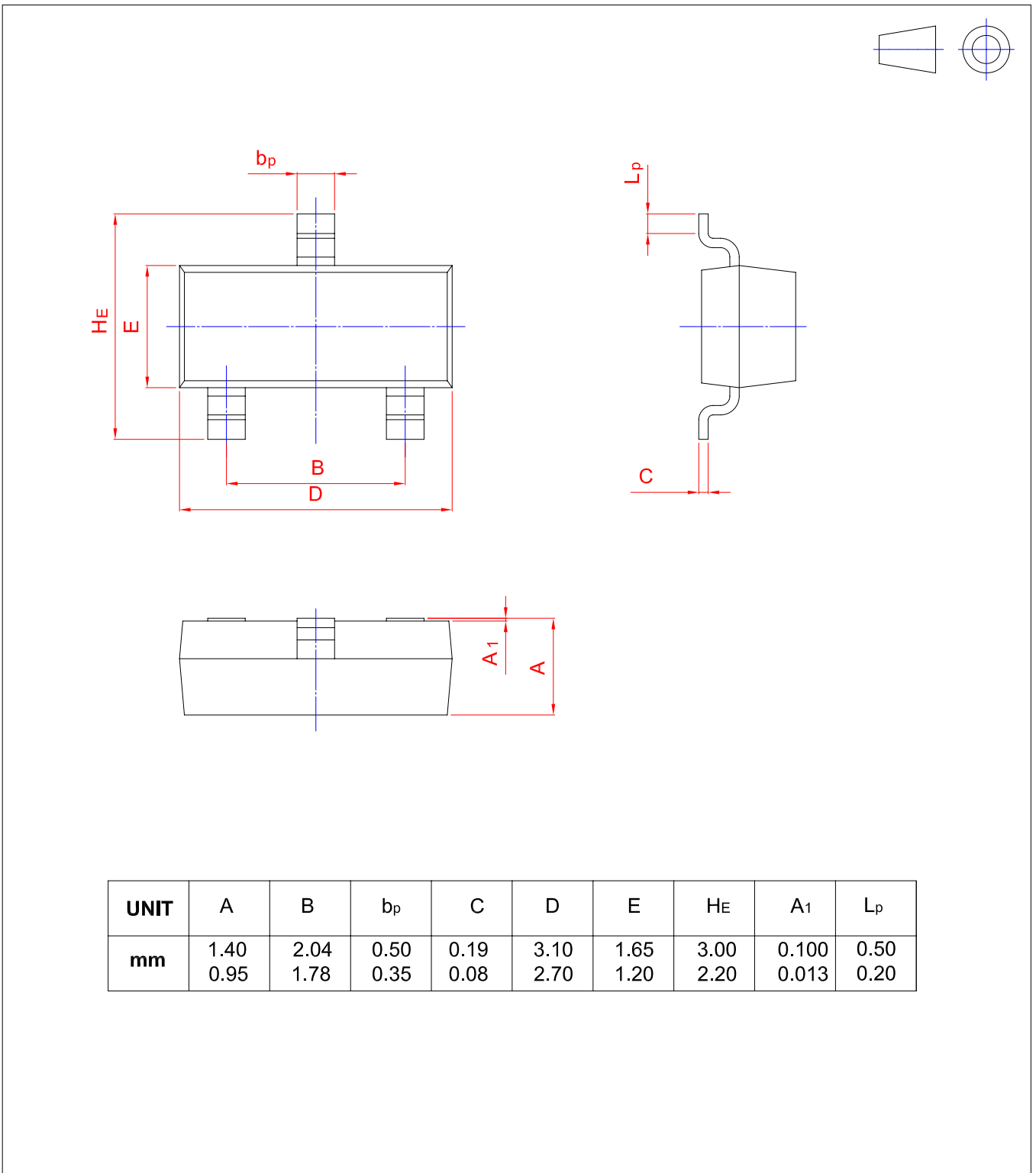


Fig. 6, Typical Emitter-Collector Characteristics

**PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT-23



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